#### SILICON (Si) POWER MOSFET A CEM3083A



# **CEM3083A**

# -30V ▲ 8.5mΩ ▲ -13A ▲ Si MOSFET

SILICON Si MOSFET ▲ SMD type P-channel enhancement mode UL94V-0 rated flame retardant epoxy SO8 package ▲ MSL 3 Super high dense cell density for extremely low R<sub>DS(ON)</sub> High power and current handling capability

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RoHS

REACH

### **MAXIMUM RATINGS**

Parameter ( $T_A = 25^{\circ}C$ , unless otherwise noted)	Characteristics	
Drain-Source Voltage	V <sub>DS</sub>	-30V
Gate-Source Voltage	V <sub>GS</sub>	±20V
Continuous Drain Current	Ι <sub>D</sub>	-13A
Pulsed Drain Current Note 1	I <sub>DM</sub>	-52A
Maximum Power Dissipation	PD	2.5W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55°C to +150°C

### **THERMAL CHARACTERISTICS**

Parameter	Symbol	Limit
Thermal Resistance, Junction-to-Ambient Note 2	R <sub>TH_JA</sub>	50°C/W

### **APPLICATIONS**

DC/DC	DC	Load	Power	USB
Converter	Fan	Switches	Banks	Storage
			4	Y

### **PIN DESCRIPTION**

Circuit Diagram	Outline • Top View	Pin No.	Description
D (5,6,7,8)		1 2 3 4	Source Source Source Gate
S (1,2,3)		5 6 7 8	Drain Drain Drain Drain

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# **ELECTRICAL CHARACTERISTICS A T**<sub>A</sub> = 25°C, unless otherwise noted

Item	Condition	Symbol	Min.	Тур.	Max.	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_{D} = -250 \mu A$	BV <sub>DSS</sub>	-30			V
Zero Gate Voltage Drain Current	$V_{DS}$ = -30V, $V_{GS}$ = 0V	I <sub>DSS</sub>			-1	μΑ
Gate Body Leakage Current, Forward	$V_{GS} = 20V, V_{DS} = 0V$	I <sub>GSSF</sub>			100	nA
Gate Body Leakage Current, Reverse	$V_{GS}$ = -20V, $V_{DS}$ = 0V	I <sub>GSSR</sub>			-100	nA
On Characteristics Note 3						
Gate Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = -250 \mu A$	V <sub>GS(th)</sub>	-1		-3	V
Static Drain-Source On-Resistance	$V_{GS} = -10V$ , $I_{D} = -10A$	R <sub>DS(ON)</sub>		8.5	10	mΩ
Static Drain-Source On-Resistance	$V_{GS} = -4.5V$ , $I_{D} = -10A$	R <sub>DS(ON)</sub>		12.3	15.5	mΩ
Dynamic Characteristics Note 4						
Input Capacitance	$V_{DS}$ = -15V, $V_{GS}$ = 0V, f = 1MHz	C <sub>ISS</sub>		2020		рF
Output Capacitance	$V_{DS}$ = -15V, $V_{GS}$ = 0V, f = 1MHz	Coss		390		рF
Reverse Transfer Capacitance	$V_{DS}$ = -15V, $V_{GS}$ = 0V, f = 1MHz	C <sub>RSS</sub>		170		рF
Switching Characteristics Note 4						
Turn-On Delay Time	$V_{\text{DD}}$ = -15V, $V_{\text{GS}}$ = -10V, $I_{\text{D}}$ = -10A, $R_{\text{G}(\text{ext})}$ = $6\Omega$	t <sub>D(ON)</sub>		18		ns
Turn-On Rise Time	$V_{\text{DD}}$ = -15V, $V_{\text{GS}}$ = -10V, $I_{\text{D}}$ = -10A, $R_{\text{G}(\text{ext})}$ = $6\Omega$	t <sub>R</sub>		8		ns
Turn-Off Delay Time	$V_{\text{DD}}$ = -15V, $V_{\text{GS}}$ = -10V, $I_{\text{D}}$ = -10A, $R_{\text{G}(\text{ext})}$ = $6\Omega$	t <sub>D(OFF)</sub>		108		ns
Turn-Off Fall Time	$V_{\text{DD}}$ = -15V, $V_{\text{GS}}$ = -10V, $I_{\text{D}}$ = -10A, $R_{G(\text{ext})}$ = $6\Omega$	t <sub>F</sub>		31		ns
Total Gate Charge	$V_{DS} = -15V, V_{GS} = -5V, I_D = -10A$	$Q_{G}$		24		nC
Gate Source Charge	$V_{DS} = -15V, V_{GS} = -5V, I_D = -10A$	Q <sub>GS</sub>		7		nC
Gate Drain Charge	$V_{DS}$ = -15V, $V_{GS}$ = -5V, $I_{D}$ = -10A	$\mathbf{Q}_{GD}$		10		nC
Drain-Source Diode Characteristics a	nd Maximum Ratings					
Drain-Source Diode Forward Current Note 2		Is			-1.3	A
Drain-Source Diode Forward Voltage <sup>Note 3</sup>	V <sub>GS</sub> = 0V, I <sub>S</sub> = -1.3A	$V_{\text{SD}}$			-1.1	v

#### Notes

1: Repetitive Rating: Pulse width limited by maximum junction temperature

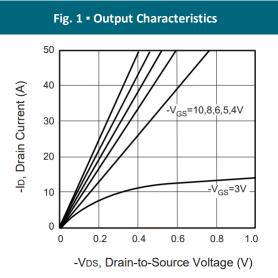
2: Surface Mounted on FR4 Board,  $t \le 10$  sec

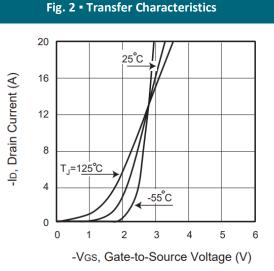
3: Pulse Test: Pulse Width  $\leq$  300µs, Duty Cycle  $\leq$  2%.

4: Guaranteed by design, not subject to production testing.



# **REFERENCE DATA ▲ TYPICAL DEVICE PERFORMANCE**





#### Fig. 3 • Capacitance

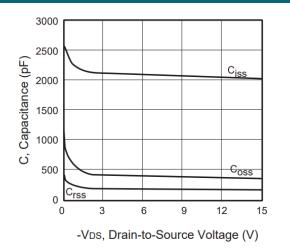
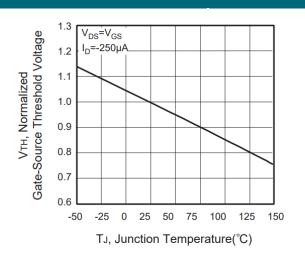
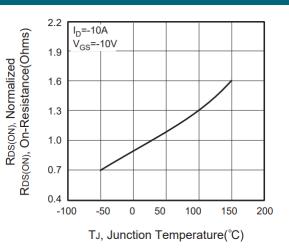


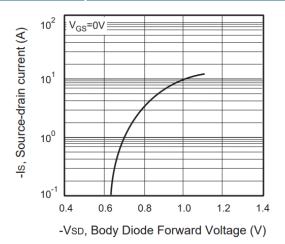
Fig. 5 • Gate Threshold Variation with Temperature



#### Fig. 4 • On-Resistance Variation with Temperature



#### Fig. 6 - Body Diode Forward Voltage Variation with Source Current



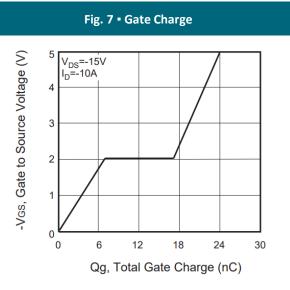
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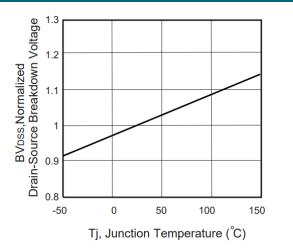
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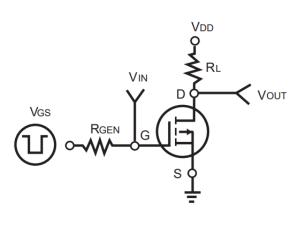
## **REFERENCE DATA A TYPICAL DEVICE PERFORMANCE**



#### Fig. 9 - Breakdown Voltage Variation vs. Temperature







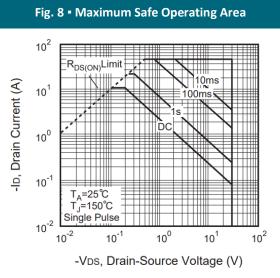
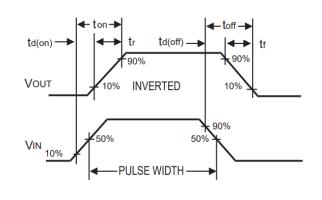


Fig. 11 - Switching Waveforms





# **REFERENCE DATA A TYPICAL DEVICE PERFORMANCE**

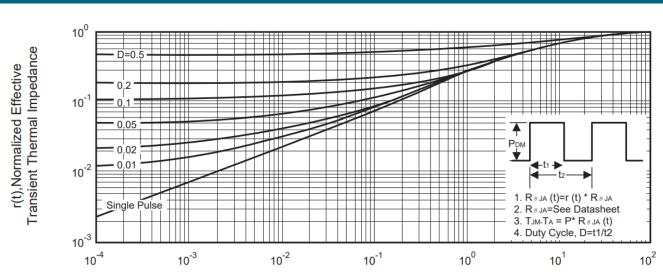
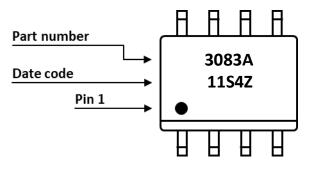


Fig. 12 • Normalized Thermal Transient Impedance Curve

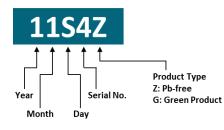
Square Wave Pulse Duration (sec)

# PART MARKING



# DATE CODE

#### Example: 11S4Z



1	2	3	4	5	6	7	8	9	Α
01	02	03	04	05	06	07	08	09	10
В	С	D	Ε	F	G	Н	I	J	K
11	12	13	14	15	16	17	18	19	20
L	Μ	Ν	0	Ρ	Q	R	S	Т	U
21	22	23	24	25	26	27	28	29	30
V									
31									

Coding list for "Day"

Coding list for "Month"

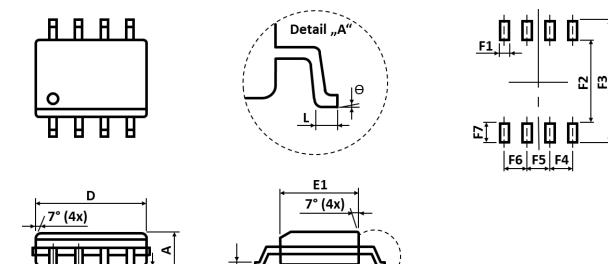


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• Detail "A"



# PACKAGE OUTLINE AND RECOMMENDED PAD LAYOUT



Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)	Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
А	1.350	-	1.750	E1	3.700		4.060
A1	0.100	-	0.250	eB	5.800		6.200
В	0.310	-	0.510	е		1.270	
С	0.170	-	0.250	L	0.400		0.950
D	4.690	-	5.000	θ	0°	-	8°
Sym	Millimeters	Millimeters	Millimeters	Sym	Millimeters	Millimeters	Millimeters

eВ

Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)	Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)	
F1	-	0.500	-	F5	-	1.270	-	
F2	-	4.250	-	F6	-	1.270	-	
F3	-	6.250	-	F7	-	1.000	-	
F4	-	1.270	-					

Notes: 1. The suggested land pattern dimensions have been provided for reference only. 2. For further information, please reference document IPC-7351A.

C

# **ORDERING INFORMATION**

В

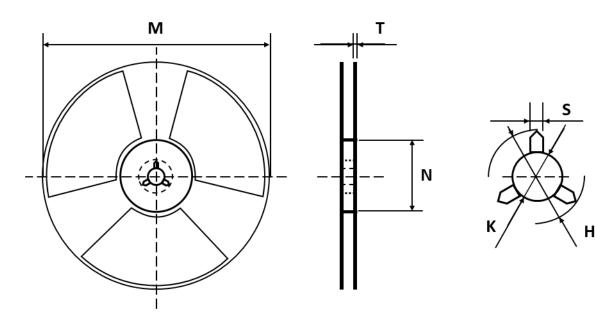
A1

Part Number	Package	Packing	Reel Qty.	Inner Box Qty.	Outer Box Qty.	
CEM3083A	SO8	13" Reel	2,500pcs	5,000pcs	40,000pcs	



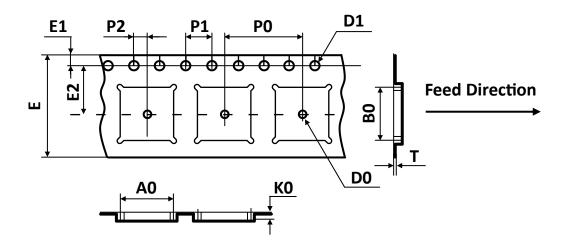


### **REEL DIMENSIONS** All dimensions in mm



Tape Size	Reel Size	М	Ν	т	Н	К	S
12mm	Ø330	Ø330.00	Ø100.00	2.20	20.00	13.20	3.00
12mm	Ø350	±2.00	±0.50	±0.20	±1.00	±0.20	±1.00

# **TAPE DIMENSIONS** All dimensions in mm



Package	A0	B0	К0	D0	D1	E	E1	E2	P0	P1	P2	т
SO8	6.50	5.30	2.05	1.50	1.50	12.00	1.75	5.50	8.00	4.00	2.00	0.25
308	±0.10	±0.10	±0.15	±0.10	±0.10	±0.10	±0.10	±0.10	±0.10	±0.10	±0.05	±0.02

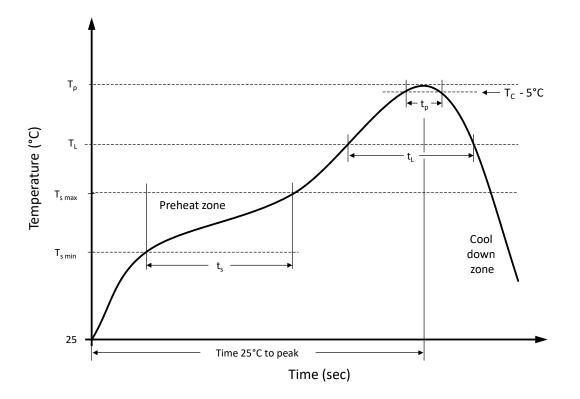
Note: All dimensions meet EIA-481-D requirements.

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## **RECOMMENDED REFLOW SOLDERING PROFILE**



#### **Recommended reflow soldering conditions** ▲ **Refer to JEDEC J-STD-020E**

Profile Features		Sn-Pb Eutetic Assembly	Pb-Free Assembly
Preheat temperature min.	$T_{smin}$	100 °C	150 °C
Preheat temperature max.	$T_{s max}$	150 °C	200 °C
Preheat time $t_s$ from $T_{s min}$ to $T_{s max}$	ts	120 seconds	120 seconds
Ramp-up rate (T <sub>L</sub> to T <sub>p</sub> )		max. 3 °C/second	max. 3 °C/second
Liquidous temperature	TL	183 °C	217 °C
Time $t_L$ maintained above $T_L$	t∟	150 seconds max.	150 seconds max.
Peak package body temperature	Tp	235°C	260°C
Timeframe of within 5°C below and up to max actual peak body temperature	t <sub>p</sub>	20 seconds max.	30 seconds max.
Ramp-down rate ( $T_L$ to $T_p$ )		max. 6 °C/second	max. 6 °C/second
Time 25°C to peak temperature		max. 6 minutes	max. 8 minutes



### **REVISION TABLE**

Revision	Date	Status	Notes
001	30/09/2022	Initial release	Initial publication

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